

BRMUR1060AC

Rev.G Jan.-2019

/ Descriptions

KF 8:

Ultrafast Recovery Diode in a TO-220AC Plastic Package.

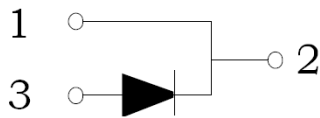
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

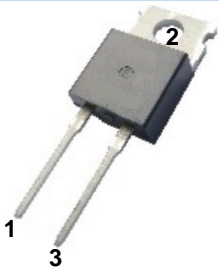
/ Applications

For high frequency, high voltage, high current rectifier diode, freewheeling diode.

/ Equivalent Circuit



/ Pinning



PIN1 2 Cathode

PIN 3 Anode

/ h_{FE} Classifications & Marking

See Marking Instructions

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Average Forward Current	I_F	1× 10	A
Peak forward surge current	I_{FSM}	100	A
Typical Thermal Resistance Junction to Case	R_{Jc}	1.5	°C/W
Junction Temperature Range	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 150	°C

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R=1mA$	600			V
Forward Voltage	V_F	$I_F=2.0A$ $T_C=25$		1.0	1.2	V
		$I_F=2.0A$ $T_C=150$		0.73	1.0	
		$I_F=10A$ $T_C=25$		1.3	1.5	
		$I_F=10A$ $T_C=150$		1.1	1.2	
Instantaneous Reverse Current(Note1)	I_R	$V_R=600V$ $T_a=25$			10	μA
		$V_R=480V$ $T_a=150$			100	
		$V_R=600V$ $T_a=150$			500	
Reverse Recovery Time	t_{rr}	$I_F=0.5A$ $I_{RR}=0.25A$ $I_R=1.0A$			50	ns

&Notes

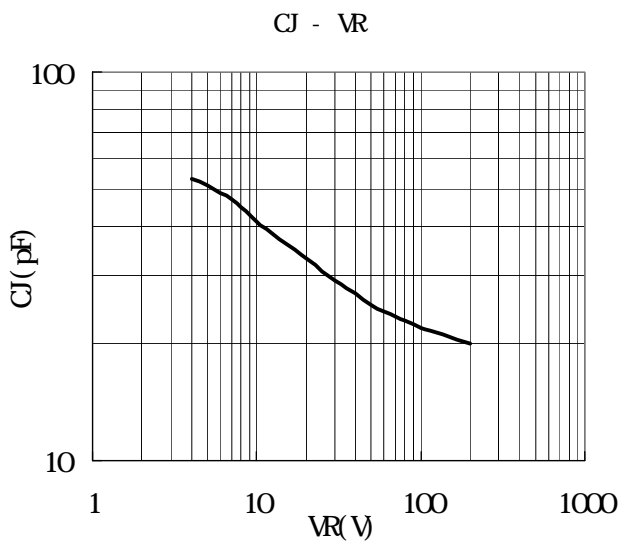
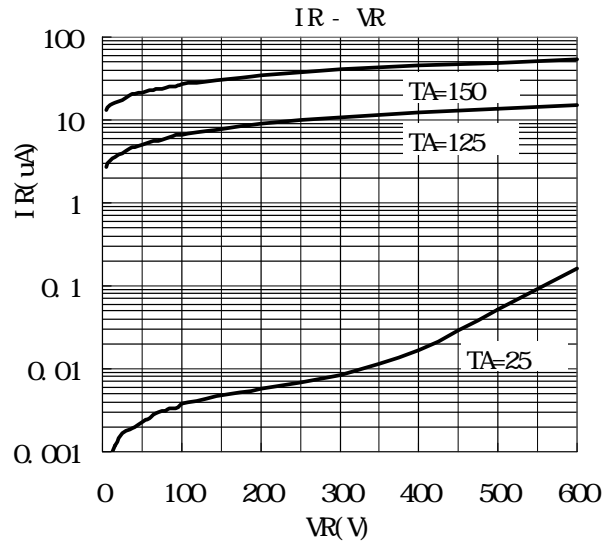
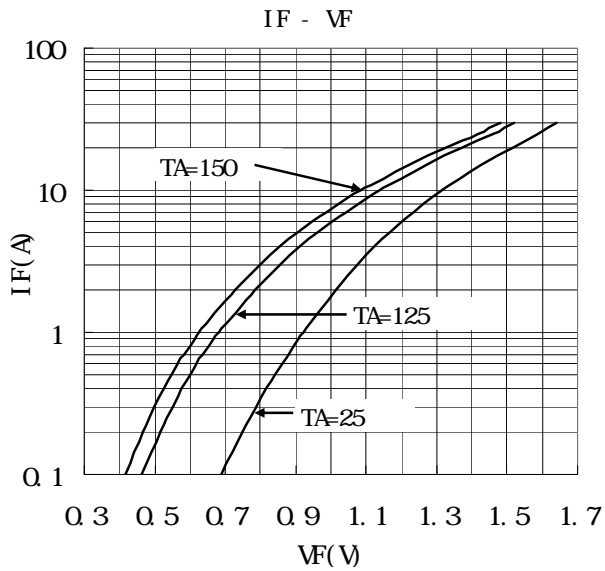
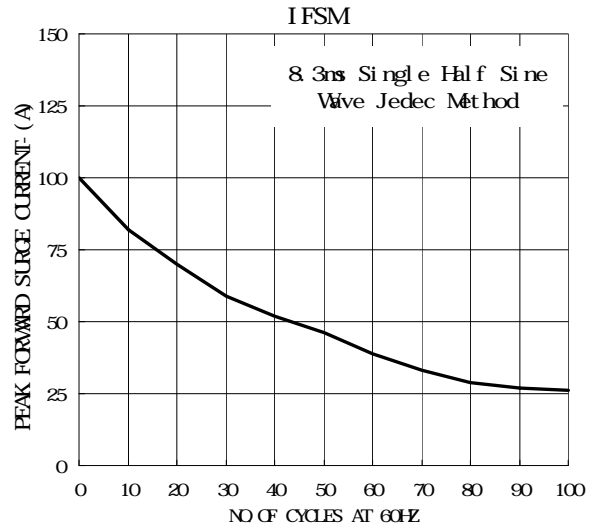
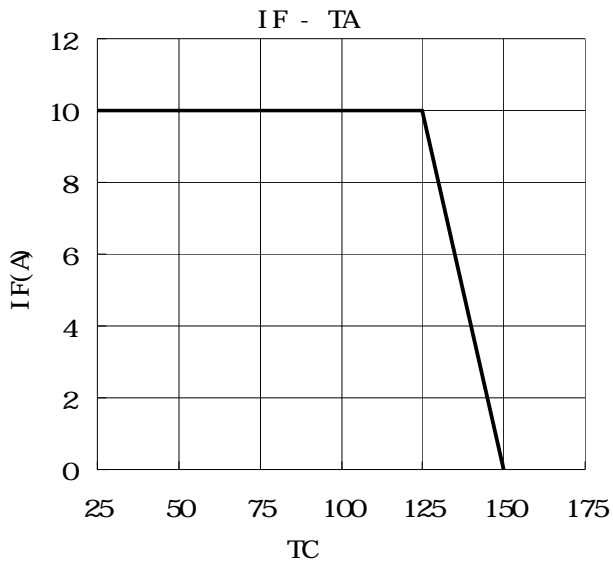
1.

2.

&Short duration pulse test used to minimize self-heating effect.

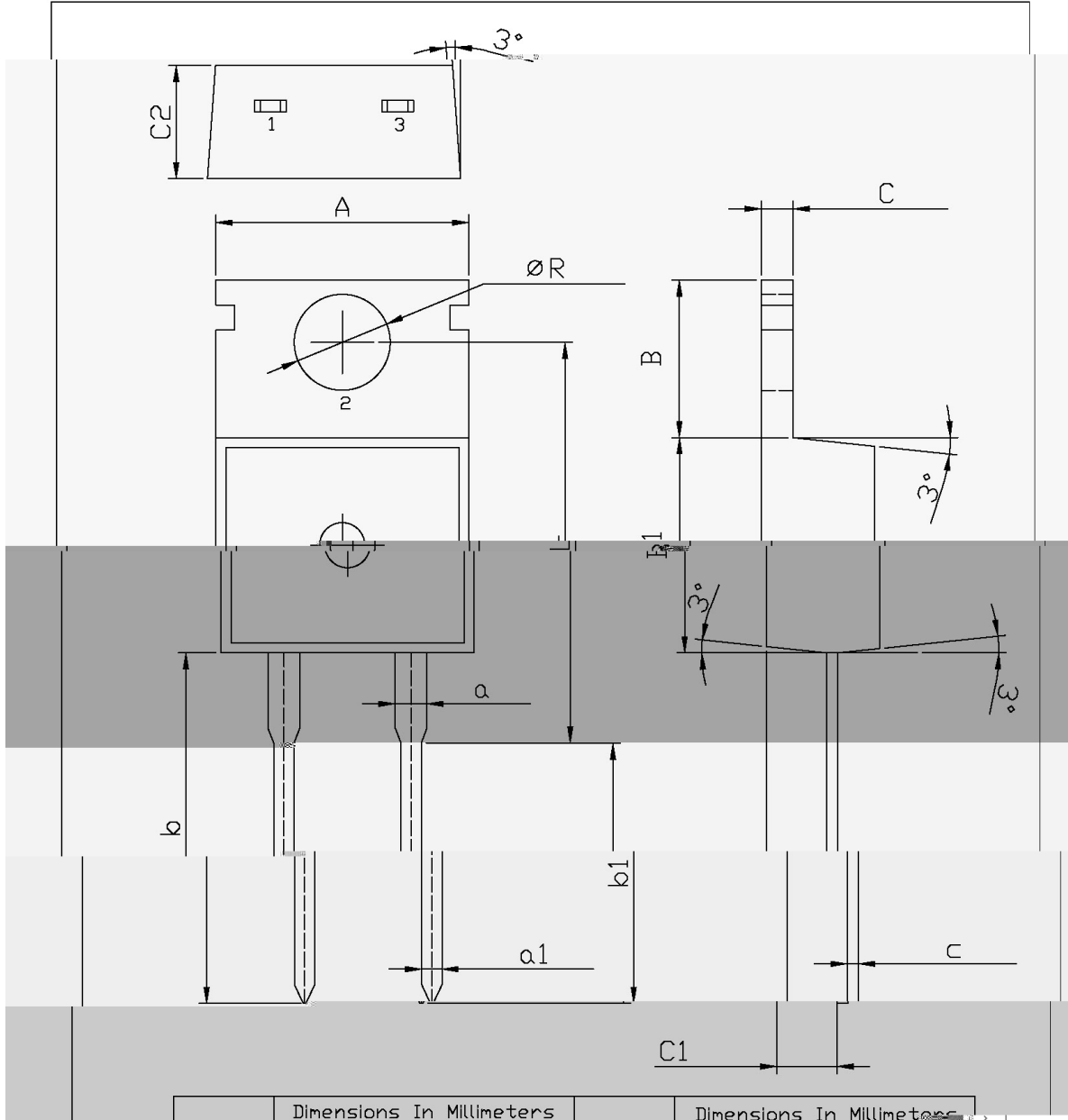
&Unless otherwise noted, values for the parameters of a single chip

/ Electrical Characteristic Curve



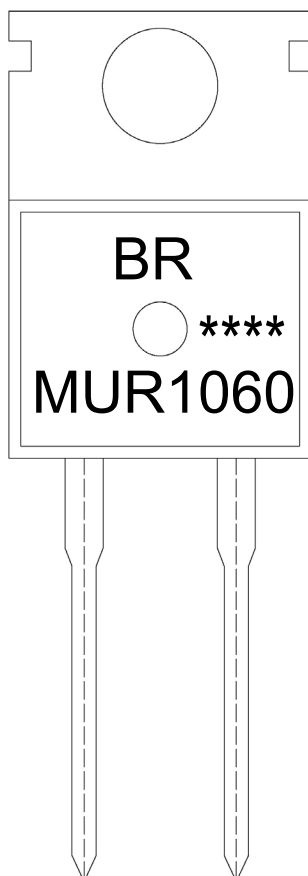
/ Package Dimensions

TO-220AC Unit:mm



Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
A ₁	9.8	10.2	B ₁	9.3	9.7
R	3.56	3.64	B1	9.0	9.4

/ Marking Instructions



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Note:

BR: Company Code

MUR1060 Product Type.

****: Lot No. Code, code change with Lot No.

